

INTERNATIONAL STANDARD

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**Power losses in voltage sourced converter (VSC) valves for high-voltage direct current (HVDC) systems –
Part 2: Modular multilevel converters**

**Pertes de puissance dans les valves à convertisseur de source de tension (VSC) des systèmes en courant continu à haute tension (CCHT) –
Partie 2: Convertisseurs multiniveaux modulaires**

<https://standards.iteh.ai/catalog/standards/iec/02524bb0-191e-43c3-b209-aad7aea76431/iec-62751-2-2014>



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POWER LOSSES IN VOLTAGE SOURCED CONVERTER (VSC) VALVES FOR HIGH-VOLTAGE DIRECT CURRENT (HVDC) SYSTEMS –

Part 2: Modular multilevel converters

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IEC 62751-2 edition 1.1 contains the first edition (2014-08) [documents 22F/303/CDV and 22F/322A/RVC] and its amendment 1 (2019-08) [documents 22F/479/CDV and 22F/488B/RVC].

In this Redline version, a vertical line in the margin shows where the technical content is modified by amendment 1. Additions are in green text, deletions are in strikethrough red text. A separate Final version with all changes accepted is available in this publication.

International Standard IEC 62751-2 has been prepared by subcommittee 22F: Power electronics for electrical transmission and distribution systems, of IEC technical committee 22: Power electronic systems and equipment.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 62751series, published under the general title *Power losses in voltage sourced converter (VSC) valves for high-voltage direct current (HVDC) systems*, can be found on the IEC website.

The committee has decided that the contents of the base publication and its amendment will remain unchanged until the stability date indicated on the IEC web site under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the publication will be

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POWER LOSSES IN VOLTAGE SOURCED CONVERTER (VSC) VALVES FOR HIGH-VOLTAGE DIRECT CURRENT (HVDC) SYSTEMS –

Part 2: Modular multilevel converters

1 Scope

This part of IEC 62751 gives the detailed method to be adopted for calculating the power losses in the valves for an HVDC system based on the “modular multi-level converter”, where each valve in the converter consists of a number of self-contained, two-terminal controllable voltage sources connected in series. It is applicable both for the cases where each modular cell uses only a single turn-off semiconductor device in each switch position, and the case where each switch position consists of a number of turn-off semiconductor devices in series (topology also referred to as “cascaded two-level converter”). The main formulae are given for the two-level “half-bridge” configuration but guidance is also given in Annex A as to how to extend the results to certain other types of MMC building block configuration.

The standard is written mainly for insulated gate bipolar transistors (IGBTs) but may also be used for guidance in the event that other types of turn-off semiconductor devices are used.

Power losses in other items of equipment in the HVDC station, apart from the converter valves, are excluded from the scope of this standard.

This standard does not apply to converter valves for line-commutated converter HVDC systems.

2 Normative references

[IEC 62751-2:2014](https://standards.iteh.ai/catalog/standards/iec/02524bb0-191e-43c3-b209-aad7aea76431/iec-62751-2-2014)

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The following documents, in whole or in part, are normatively referenced in this document and are indispensable for its application. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60633, *Terminology for high-voltage direct-current (HVDC) transmission*

IEC 61803, *Determination of power losses in high-voltage direct current (HVDC) converter stations*

IEC 62747, *Terminology for voltage-sourced converters (VSC) for high-voltage direct current (HVDC) systems*

IEC 62751-1:2014, *Power losses in voltage sourced converter (VSC) valves for high-voltage direct current (HVDC) systems – Part 1: General requirements*

ISO/IEC Guide 98-3, *Uncertainty of measurement – Part 3: Guide to the expression of uncertainty in measurement (GUM:1995)*

3 Terms, definitions, symbols and abbreviated terms

For the purposes of this document, the terms and definitions given in IEC 60633, IEC 62747, IEC 62751-1, as well as the following apply.

3.1 Terms and definitions

3.1.1

modular multi-level converter

MMC

multi-level converter in which each VSC valve consists of a number of MMC building blocks connected in series

Note 1 to entry: This note applies to the French language only.

3.1.2

MMC building block

self-contained, two-terminal controllable voltage source together with d.c. capacitor(s) and immediate auxiliaries, forming part of a MMC

3.1.3

IGBT-diode pair

arrangement of IGBT and free-wheeling diode connected in inverse parallel

3.1.4

switch position

semiconductor function which behaves as a single, indivisible switch

Note 1 to entry: A switch position may consist of a single IGBT-diode pair or, in the case of the cascaded two level converter, a series connection of multiple IGBT-diode pairs.

3.1.5

cascaded two-level converter

CTL

modular multi-level converter in which each switch position consists of more than one IGBT-diode pair connected in series

Note 1 to entry: This note applies to the French language only.

3.1.6

submodule

MMC building block where each switch position consists of only one IGBT-diode pair

3.1.7

cell

MMC building block where each switch position consists of more than one IGBT-diode pair connected in series

3.1.8

turn-off semiconductor device

controllable semiconductor device which may be turned on and off by a control signal, for example an IGBT

3.1.9

insulated gate bipolar transistor

IGBT

turn-off semiconductor device with three terminals: a gate terminal (G) and two load terminals emitter (E) and collector (C)

Note 1 to entry: This note applies to the French language only.

3.1.10

operating state

condition in which the HVDC substation is energized and the converters are de-blocked

Note 1 to entry: Unlike line-commutated converter, VSC can operate with zero active/reactive power output.

3.1.11

no-load operating state

condition in which the HVDC substation is energized but the IGBTs are blocked and all necessary substation service loads and auxiliary equipment are connected

Note 1 to entry: In the no-load state, in principle no switching should occur as the valve is blocked. However, in some designs, it may be necessary to make occasional switching operations to balance voltages between different parts of the converter. Here, some losses may occur and need to be accounted for.

3.1.12

idling operating state

condition in which the HVDC substation is energized and the IGBTs are de-blocked but with no active or reactive power output at the point of common connection to the a.c. network

Note 1 to entry: The “idling operating” and “no-load” conditions are similar but from the no-load state, several seconds may be needed before power can be transmitted, while from the idling operating state, power transmission may be commenced almost immediately (less than 3 power frequency cycles).

Note 2 to entry: In the idling operating state, the converter is capable of actively controlling the d.c. voltage, in contrast to the no-load state where the behavior of the converter is essentially “passive”.

Note 3 to entry: Losses will generally be slightly lower in the no-load state than in the idling operating state, therefore this operating mode is preferred where the arrangement of the VSC system permits it.

3.1.13

modulation index of PWM converters

M

ratio of the peak line to ground a.c. converter voltage, to half of the converter d.c. terminal to terminal voltage

$$M = \frac{\sqrt{2} \cdot U_{c1}}{\sqrt{3} \cdot \frac{U_{dc}}{2}}$$

where

U_{c1} is the r.m.s value of the fundamental frequency component of the line-to-line voltage U_c ;

U_c is the output voltage of one VSC phase unit at its a.c. terminal;

U_{dc} is the output voltage of one VSC phase unit at its d.c. terminals.

Note 1 to entry: Some sources define modulation index in a different way such that a modulation index of 1 refers to a square-wave output, which means that the modulation index can never exceed 1. The modulation index according to that definition is given simply by $M \cdot (\pi/4)$. However, that definition is relevant mainly to two-level converters using PWM.

3.2 Symbols and abbreviated terms

3.2.1 Valve and simulation data

N_{tc}	number of MMC building blocks per valve
N_c	number of series-connected semiconductor devices per switch position
N_{sr}	total number of series resistive elements contributing to conduction losses in the valve, other than in the IGBTs and diodes
N_{cv}	number of d.c. capacitors in the valve
N_s	number of switching cycles (on or off) experienced by each VSC valve level during the integration time t_i
N_{pr}	total number of parallel resistive elements contributing to d.c. voltage dependent losses in the valve
N_{sn}	number of snubber circuits per valve

t_i integration time used in the simulation

3.2.2 Semiconductor device characteristics

V_{0T}	average IGBT threshold voltage for the relevant operating conditions
R_{0T}	average IGBT slope resistance for the relevant operating conditions, valid at the device terminals
V_{0D}	average diode threshold voltage for the relevant operating conditions
R_{0D}	average diode slope resistance for the relevant operating condition, valid at the device terminals
E_{on}	average turn-on energy dissipated in the IGBT for the relevant operating conditions
E_{off}	average turn-off energy dissipated in the IGBT(s) for the relevant operating conditions
$E_{on,T1_j,k}$	turn-on energy dissipated in IGBT T1 in the j^{th} MMC building block for the k^{th} turn-on event for the relevant operating conditions (voltage, current and junction temperature)
$E_{on,T2_j,k}$	turn-on energy dissipated in IGBT T2 in the j^{th} MMC building block for the k^{th} turn-on event for the relevant operating conditions (voltage, current and junction temperature)
$E_{off,T1_j,k}$	turn-off energy dissipated in IGBT T1 in the j^{th} MMC building block for the k^{th} turn-off event for the relevant operating conditions (voltage, current and junction temperature)
$E_{off,T2_j,k}$	turn-off energy dissipated in IGBT T2 in the j^{th} MMC building block for the k^{th} turn-off event for the relevant operating conditions (voltage, current and junction temperature)
$E_{rec,D1_j,k}$	diode recovery energy dissipated in diode D1 in the j^{th} MMC building block for the k^{th} diode turn-off event for the relevant operating conditions (voltage, current and junction temperature)
$E_{rec,D2_j,k}$	diode recovery energy dissipated in diode D2 in the j^{th} MMC building block for the k^{th} diode turn-off event for the relevant operating conditions (voltage, current and junction temperature)

3.2.3 Other component characteristics

R_{s_k}	total resistance of the k^{th} series resistive elements in the valve contributing to other conduction losses
R_{dc_k}	resistance of the k^{th} parallel resistive component in the valve
R_{ESR_j}	average equivalent series resistance of the j^{th} d.c. capacitor
$E_{sn,on_j,k}$	energy dissipated in the snubber resistor of the j^{th} snubber circuit for the k^{th} turn-on event for the relevant operating conditions (voltage, and current where relevant to the design of the snubber)
$E_{sn,off_j,k}$	energy dissipated in the snubber resistor of the j^{th} snubber circuit for the k^{th} turn-off event for the relevant operating conditions (voltage, and current where relevant to the design of the snubber)

3.2.4 Operating parameters

I_{T1av_j}	mean current of IGBT T1 in the j^{th} MMC building block, averaged over an integration time t_i
I_{T2av_j}	mean current of IGBT T2 in the j^{th} MMC building block, averaged over an integration time t_i
I_{T1rms_j}	rms current of IGBT T1 in the j^{th} MMC building block, averaged over an integration time t_i
I_{T2rms_j}	rms current of IGBT T2 in the j^{th} MMC building block, averaged over an integration time t_i